

Silicon PNP Power Transistors

2SB1016

DESCRIPTION

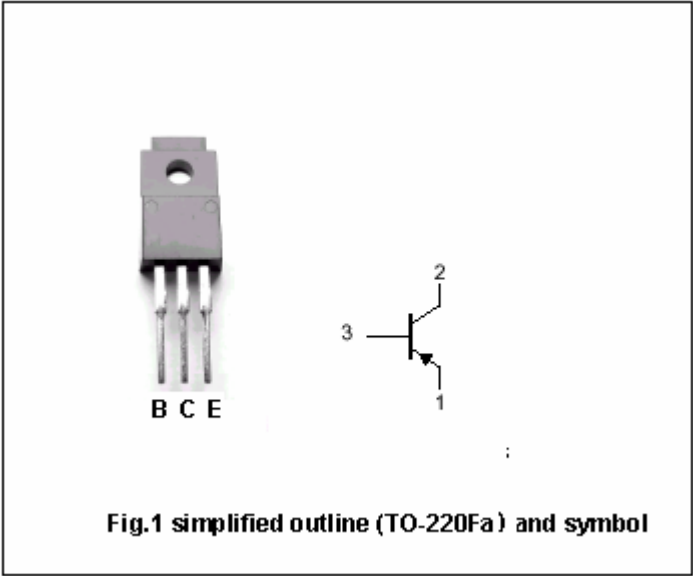
- With TO-220Fa package
- High breakdown voltage
- Low collector saturation voltage
- Complement to type 2SD1407

APPLICATIONS

- Power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector -emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-5	A
I _B	Base current		-0.5	A
P _C	Collector power dissipation	T _C =25	30	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SB1016

CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-100			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-4A; I_B=-0.4A$			-2.0	V
V_{BE}	Base-emitter voltage	$I_C=-4A; V_{CE}=-5V$			-1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100V; I_E=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-1	mA
h_{FE-1}	DC current gain	$I_C=-1A; V_{CE}=-5V$	40		240	
h_{FE-2}	DC current gain	$I_C=-4A; V_{CE}=-5V$	20			
f_T	Transition frequency	$I_C=-1A; V_{CE}=-5V$		5		MHz
C_{OB}	Collector output capacitance	$f=1MHz; V_{CB}=-10V; I_E=0$		270		pF

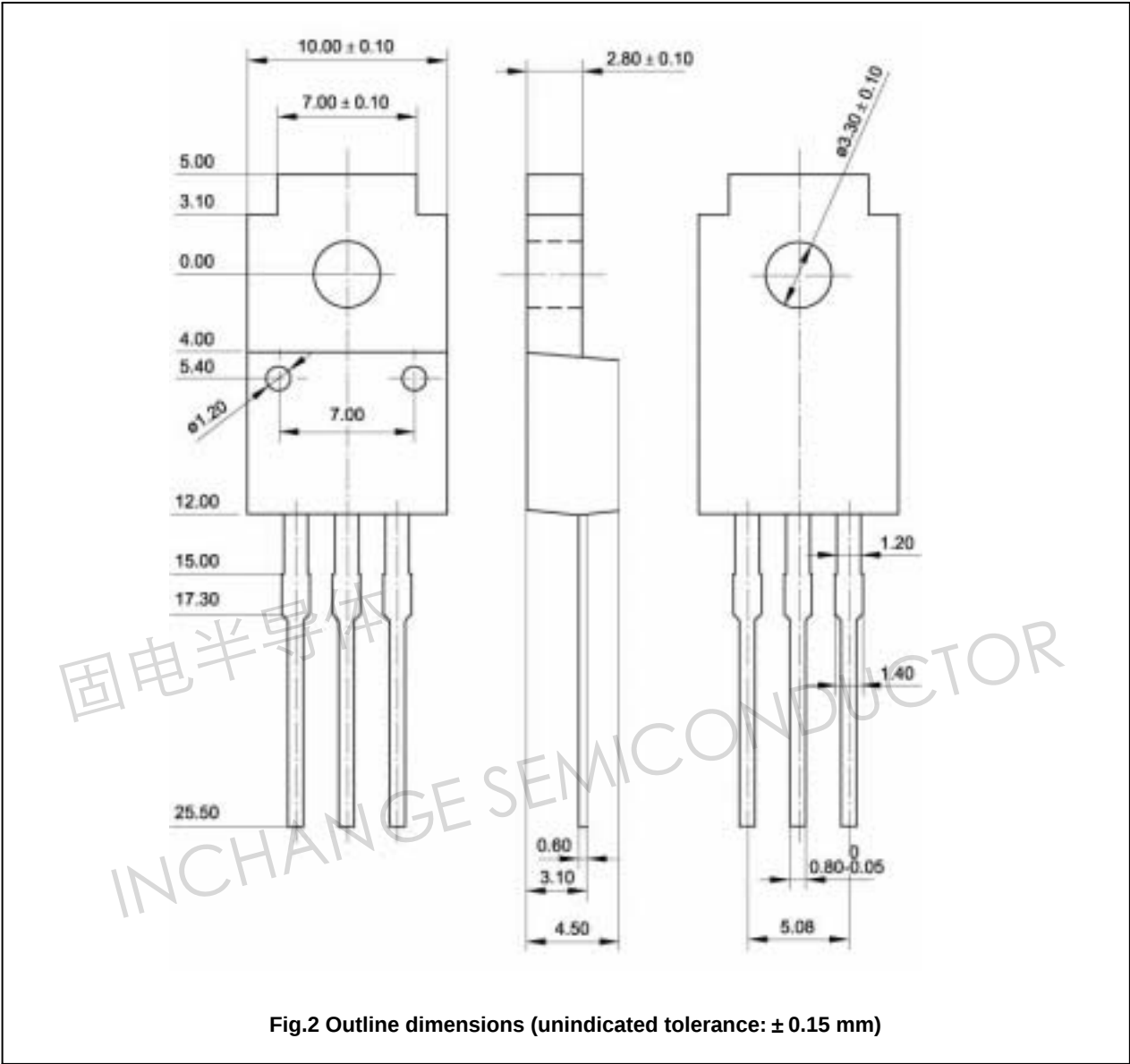
◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240

Silicon PNP Power Transistors

2SB1016

PACKAGE OUTLINE



Silicon PNP Power Transistors

2SB1016

